

Test Report

號碼(No.): ETR23405084 日期(Date): 02-May-2023

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穩懋半導體股份有限公司 (WIN SEMICONDUCTORS CORP.)

桃園市龜山區華亞科技園區科技七路35號 (NO.35, KEJI 7TH RD., HWAYA TECHNOLOGY PARK, GUISHAN DISTRICT, TAOYUAN CITY 33383, TAIWAN)

以下測試樣品係由申請廠商所提供及確認 (The following sample(s) was/were submitted and identified by the applicant as):

送樣廠商(Sample Submitted By)

: 穩懋半導體股份有限公司 (WIN SEMICONDUCTORS CORP.)

樣品名稱(Sample Name)

: pHEMT WAFER

收件日(Sample Receiving Date)

: 21-Apr-2023

測試期間(Testing Period)

: 21-Apr-2023 to 28-Apr-2023

測試需求(Test Requested)

(1) 依據客戶指定、參考RoHS 2011/65/EU Annex II及其修訂指令(EU) 2015/863測試 鎬、鉛、汞、六價鉻、多溴聯苯、多溴聯苯醚, DBP, BBP, DEHP, DIBP。 (As specified by client, with reference to RoHS 2011/65/EU Annex II and amending Directive (EU) 2015/863 to determine Cadmium, Lead, Mercury, Cr(VI), PBBs, PBDEs, DBP, BBP, DEHP, DIBP contents in the submitted sample(s).)

(2) 其他測試項目請見下一頁。 (Please refer to next pages for the other item(s).)

測試結果(Test Results)

請參閱下一頁 (Please refer to following pages.)

結 論(Conclusion)

1) 根據客戶所提供的樣品,其編、鉛、汞、六價鉻、多溴聯苯、多溴聯苯醚, DBP, BBP, DEHP, DIBP的測試結果符合RoHS 2011/65/EU Annex II暨其修訂指令(EU) 2015/863之限值要求。 (Based on the performed tests on submitted sample(s), the test results of Cadmium, Lead, Mercury, Cr(VI), PBBs, PBDEs, DBP, BBP, DEHP, DIBP comply with the limits as set by RoHS Directive (EU) 2015/863 amending Annex II to Directive 2011/65/EU.)

Troy Chang / Department Malager
Signed for and on behalf of AIWAN LTD.
Chemical Laboratory - Taipei



PIN CODE: 32FF1224



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測試部位敘述 (Test Part Description)

No.1 : 晶圓 (WAFER)

測試結果 (Test Results)

測試項目	測試方法	單位	MDL	結果	限值
(Test Items)	(Method)	(Unit)		(Result)	(Limit)
				No.1	
鎘 (Cd) (Cadmium (Cd))	參考IEC 62321-5: 2013·以感應耦合電漿發射 光譜儀分析。(With reference to IEC 62321-5: 2013, analysis was performed by ICP-OES.)	mg/kg	2	n.d.	100
鉛 (Pb) (Lead (Pb))		mg/kg	2	n.d.	1000
汞 (Hg) (Mercury (Hg))	參考IEC 62321-4: 2013+ AMD1: 2017 · 以感應 耦合電漿發射光譜儀分析。(With reference to IEC 62321-4: 2013+ AMD1: 2017, analysis was performed by ICP-OES.)	mg/kg	2	n.d.	1000
六價鉻 Cr(VI) (Hexavalent Chromium Cr(VI))	參考IEC 62321-7-2: 2017·以紫外光-可見光分 光光度計分析。(With reference to IEC 62321- 7-2: 2017, analysis was performed by UV- VIS.)	mg/kg	8	n.d.	1000
一溴聯苯 (Monobromobiphenyl)		mg/kg	5	n.d.	_
二溴聯苯 (Dibromobiphenyl)		mg/kg	5	n.d.	_
三溴聯苯 (Tribromobiphenyl)		mg/kg	5	n.d.	-
四溴聯苯 (Tetrabromobiphenyl)		mg/kg	5	n.d.	-
五溴聯苯 (Pentabromobiphenyl)	参考IEC 62321-6: 2015·以氣相層析儀/質譜儀	mg/kg	5	n.d.	-
六溴聯苯 (Hexabromobiphenyl)	分析。(With reference to IEC 62321-6: 2015,	mg/kg	5	n.d.	-
七溴聯苯 (Heptabromobiphenyl)	analysis was performed by GC/MS.)	mg/kg	5	n.d.	_
八溴聯苯 (Octabromobiphenyl)	1	mg/kg	5	n.d.	-
九溴聯苯 (Nonabromobiphenyl)]	mg/kg	5	n.d.	-
十溴聯苯 (Decabromobiphenyl)		mg/kg	5	n.d.	-
多溴聯苯總和 (Sum of PBBs)		mg/kg	-	n.d.	1000



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測試項目	測試方法	單位	MDL	結果	限值
(Test Items)	(Method)	(Unit)		(Result)	(Limit)
				No.1	
一溴聯苯醚 (Monobromodiphenyl ether)		mg/kg	5	n.d.	-
二溴聯苯醚 (Dibromodiphenyl ether)		mg/kg	5	n.d.	-
三溴聯苯醚 (Tribromodiphenyl ether)		mg/kg	5	n.d.	-
四溴聯苯醚 (Tetrabromodiphenyl ether)		mg/kg	5	n.d.	-
五溴聯苯醚 (Pentabromodiphenyl ether)	参考IEC 62321-6: 2015,以氣相層析儀/質譜儀	mg/kg	5	n.d.	-
六溴聯苯醚 (Hexabromodiphenyl ether)	分析。(With reference to IEC 62321-6: 2015,	mg/kg	5	n.d.	-
七溴聯苯醚 (Heptabromodiphenyl ether)	analysis was performed by GC/MS.)	mg/kg	5	n.d.	-
八溴聯苯醚 (Octabromodiphenyl ether)		mg/kg	5	n.d.	-
九溴聯苯醚 (Nonabromodiphenyl ether)		mg/kg	5	n.d.	-
十溴聯苯醚 (Decabromodiphenyl ether)		mg/kg	5	n.d.	-
多溴聯苯醚總和 (Sum of PBDEs)		mg/kg	-	n.d.	1000
鄰苯二甲酸丁苯甲酯 (BBP) (Butyl benzyl phthalate (BBP))		mg/kg	50	n.d.	1000
					1000
鄰苯二甲酸二丁酯 (DBP) (Dibutyl phthalate (DBP))	參考IEC 62321-8: 2017·以氣相層析儀/質譜儀 分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.	1000
鄰苯二甲酸二(2-乙基己基)酯 (DEHP) (Di- (2-ethylhexyl) phthalate (DEHP))		mg/kg	50	n.d.	1000
鄰苯二甲酸二異丁酯 (DIBP) (Diisobutyl phthalate (DIBP))		mg/kg	50	n.d.	1000
鄰苯二甲酸二異癸酯 (DIDP) (Diisodecyl phthalate (DIDP)) (CAS No.: 26761-40-0, 68515-49-1)		mg/kg	50	n.d.	-
鄰苯二甲酸二異壬酯 (DINP) (Diisononyl phthalate (DINP)) (CAS No.: 28553-12-0, 68515-48-0)		mg/kg	50	n.d.	-
鄰苯二甲酸二正辛酯 (DNOP) (Di-n-octyl phthalate (DNOP)) (CAS No.: 117-84-0)		mg/kg	50	n.d.	-



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測試項目	測試方法	單位	MDL	結果	限值
(Test Items)	(Method)	(Unit)		(Result)	(Limit)
				No.1	
氯 (Cl) (Chlorine (Cl)) (CAS No.: 22537- 15-1)	參考BS EN 14582: 2016 · 以離子層析儀分析。 (With reference to BS EN 14582: 2016, analysis was performed by IC.)	mg/kg	50	n.d.	-
溴 (Br) (Bromine (Br)) (CAS No.: 10097- 32-2)	參考BS EN 14582: 2016 · 以離子層析儀分析。 (With reference to BS EN 14582: 2016, analysis was performed by IC.)	mg/kg	50	n.d.	-

備註(Note):

- 1. mg/kg = ppm; 0.1wt% = 0.1% = 1000ppm
- 2. MDL = Method Detection Limit (方法偵測極限值)
- 3. n.d. = Not Detected (未檢出); 小於MDL / Less than MDL
- 4. "-" = Not Regulated (無規格值)
- 5. 除非另有說明,參照ILAC-G8:09/2019,採用簡單二元(w=0)允收規則進行符合性判定;根據此規則,符合性結果之判定係以測試結果與限值做比較。(Unless otherwise stated, the decision rule for conformity reporting is based on Binary Statement for Simple Acceptance Rule (w=0) stated in ILAC-G8:09/2019. According to this rule, the judgement of conformity is based on the comparing test results with limits.)



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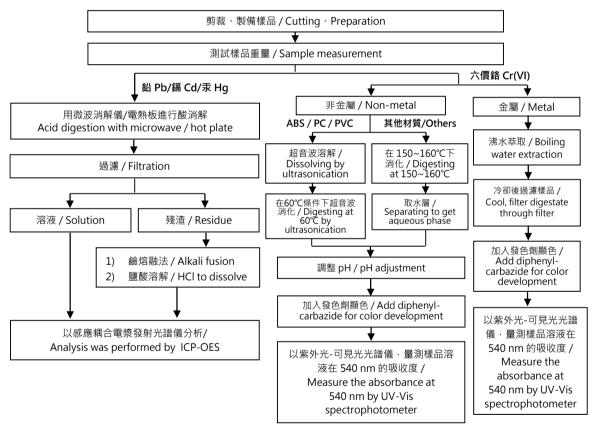
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重金屬流程圖 / Analytical flow chart of heavy metal

根據以下的流程圖之條件,樣品已完全溶解。(六價鉻測試方法除外)

These samples were dissolved totally by pre-conditioning method according to below flow chart. (Cr^{6+} test method excluded)





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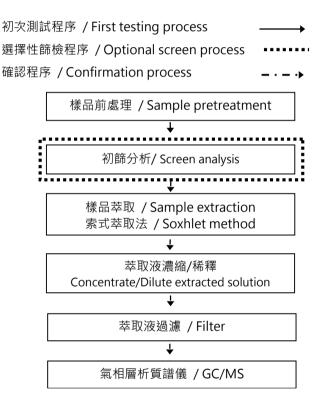
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多溴聯苯/多溴聯苯醚分析流程圖 / Analytical flow chart - PBBs/PBDEs





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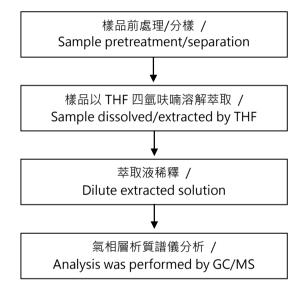
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可塑劑分析流程圖 / Analytical flow chart - Phthalate

【測試方法/Test method: IEC 62321-8】





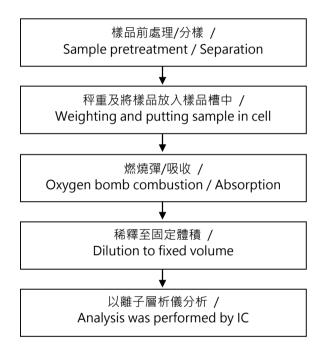
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鹵素分析流程圖 / Analytical flow chart - Halogen





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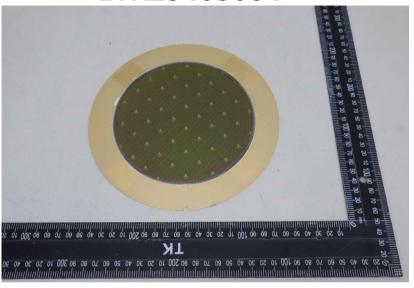
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* 照片中如有箭頭標示,則表示為實際檢測之樣品/部位. * (The tested sample / part is marked by an arrow if it's shown on the photo.)

ETR23405084



** 報告結尾 (End of Report) **